

ABSTRACT OF THE DISCLOSURE

To provide a highly reliable complementary thin film transistor circuit in which deviations in characteristics of a first-conductivity-type thin film transistor and a second-conductivity-type thin film transistor can be reduced or prevented and operated stably. A first-conductivity-type thin film transistor and a second-conductivity-type thin film transistor are formed using single crystal grains, the single crystal grains being formed substantially centered on each of a plurality of starting-point portions provided on an insulating surface of a substrate, wherein the first-conductivity-type thin film transistor and the second-conductivity-type thin film transistor are formed by equalizing their drain current directions, and are formed in the single crystal grains in which at least channel regions of the first-conductivity-type thin film transistor and the second-conductivity-type thin film transistor have the same plane orientation.